BLM7G1822S-80PB; BLM7G1822S-80PBG LDMOS 2-stage power MMIC

AMPLEON

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Product data sheet

Product profile

1.1 General description

The BLM7G1822S-80PB(G) is a dual section, 2-stage power MMIC using Ampleon's state of the art GEN7 LDMOS technology. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 1805 MHz to 2170 MHz. Available in gull wing or straight lead outline.

Table 1. **Performance**

Typical RF performance at T_{case} = 25 °C. Test signal: 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF; per section unless otherwise specified in a class-AB production circuit.

| Test signal | f | I _{Dq1} [1] | I _{Dq2} [1] | V _{DS} | P _{L(AV)} | Gp | η _D | ACPR _{5M} |
|-----------------------|--------|----------------------|----------------------|-----------------|--------------------|------|----------------|--------------------|
| | (MHz) | (mA) | (mA) | (V) | (W) | (dB) | (%) | (dBc) |
| single carrier W-CDMA | 2167.5 | 80 | 240 | 28 | 8 | 28 | 24 | -36 |

^[1] I_{Da1} represents driver stage; I_{Da2} represents final stage.

1.2 Features and benefits

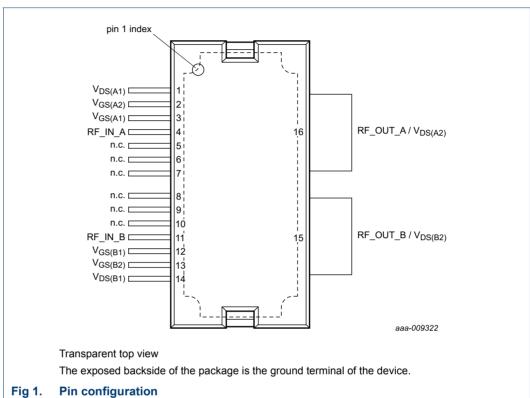
- Designed for broadband operation (frequency 1805 MHz to 2170 MHz)
- High section-to-section isolation enabling multiple combinations
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- RF power MMIC for W-CDMA base stations in the 1805 MHz to 2170 MHz frequency range. Possible circuit topologies are the following as also depicted in Section 8.1:
 - Dual section or single ended
 - Doherty
 - Quadrature combined
 - Push-pull

Pinning information 2.

Pinning 2.1



2.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|---------------------|-----|--|
| V _{DS(A1)} | 1 | drain-source voltage of section A, driver stage (A1) |
| V _{GS(A2)} | 2 | gate-source voltage of section A, final stage (A2) |
| V _{GS(A1)} | 3 | gate-source voltage of section A, driver stage (A1) |
| RF_IN_A | 4 | RF input section A |
| n.c. | 5 | not connected |
| n.c. | 6 | not connected |
| n.c. | 7 | not connected |
| n.c. | 8 | not connected |
| n.c. | 9 | not connected |
| n.c. | 10 | not connected |
| RF_IN_B | 11 | RF input section B |
| V _{GS(B1)} | 12 | gate-source voltage of section B, driver stage (B1) |
| V _{GS(B2)} | 13 | gate-source voltage of section B, final stage (B2) |
| V _{DS(B1)} | 14 | drain-source voltage of section B, driver stage (B1) |

Table 2. Pin description ... continued

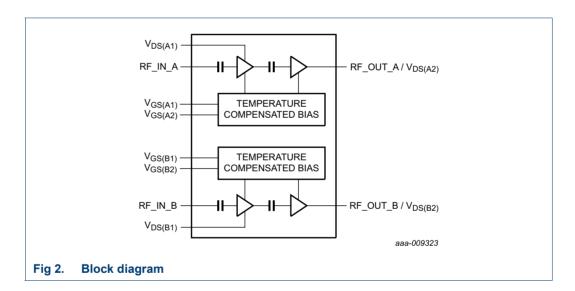
| Symbol | Pin | Description |
|------------------------------|--------|---|
| RF_OUT_B/V _{DS(B2)} | 15 | RF output section B / drain-source voltage of section B, final stage (B2) |
| RF_OUT_A/V _{DS(A2)} | 16 | RF output section A / drain-source voltage of section A, final stage (A2) |
| GND | flange | RF ground |

3. Ordering information

Table 3. Ordering information

| Type number | Package | kage | | | | | | | | |
|------------------|---------|---|-----------|--|--|--|--|--|--|--|
| | Name | Description | Version | | | | | | | |
| BLM7G1822S-80PB | HSOP16F | plastic, heatsink small outline package; 16 leads(flat) | SOT1211-2 | | | | | | | |
| BLM7G1822S-80PBG | HSOP16 | plastic, heatsink small outline package; 16 leads | SOT1212-2 | | | | | | | |

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|----------------------|------------|------|------|------|
| V_{DS} | drain-source voltage | | - | 65 | V |
| V_{GS} | gate-source voltage | | -0.5 | +13 | V |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | [1] | - | 225 | °C |
| T _{case} | case temperature | | - | 150 | °C |

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

| Symbol | Parameter | Conditions | Value | Unit |
|----------------------|--|---|-------|------|
| R _{th(j-c)} | thermal resistance from junction to case | final stage; $T_{case} = 90 ^{\circ}\text{C}$; $P_L = 5.04 \text{W}$ | 0.8 | K/W |
| | | driver stage; $T_{case} = 90 \text{ °C}$; $P_L = 5.04 \text{ W}$ | 2.8 | K/W |

^[1] When operated with a CW signal.

7. Characteristics

Table 6. DC characteristics

 T_{case} = 25 °C; per section unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------|--|---|-----|-----|-----|------|
| Final sta | ge | | | ' | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 0.604 \text{ mA}$ | 65 | - | - | V |
| V_{GSq} | gate-source quiescent voltage | V _{DS} = 28 V; I _D = 240 mA | 1.6 | 2.0 | 2.5 | V |
| | | V _{DS} = 28 V; I _D = 240 mA [1] | 2.1 | 2.8 | 3.6 | V |
| $\Delta I_{Dq}/\Delta T$ | quiescent drain current variation with temperature | $-40 ^{\circ}\text{C} \le T_{case} \le +85 ^{\circ}\text{C}$ | - | 2 | - | % |
| I _{DSS} | drain leakage current | V _{GS} = 0 V; V _{DS} = 28 V | - | - | 1.4 | μΑ |
| I _{DSX} | drain cut-off current | V _{GS} = 5.65 V; V _{DS} = 10 V | - | 11 | - | Α |
| I _{GSS} | gate leakage current | V _{GS} = 1.0 V; V _{DS} = 0 V | - | - | 140 | nA |
| Driver st | age | | | ' | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 0.116 \text{ mA}$ | 65 | - | - | V |
| V_{GSq} | gate-source quiescent voltage | V_{DS} = 28 V; I_{D} = 80 mA | 1.7 | 2.1 | 2.6 | V |
| | | $V_{DS} = 28 \text{ V}; I_D = 80 \text{ mA}$ | 2.1 | 2.7 | 3.4 | V |
| $\Delta I_{Dq}/\Delta T$ | quiescent drain current variation with temperature | $-40 ^{\circ}\text{C} \le T_{case} \le +85 ^{\circ}\text{C}$ [2] | - | 2 | - | % |
| I _{DSS} | drain leakage current | V _{GS} = 0 V; V _{DS} = 28 V | - | - | 1.4 | μΑ |
| I _{DSX} | drain cut-off current | V _{GS} = 5.65 V; V _{DS} = 10 V | - | 1.9 | - | Α |
| I _{GSS} | gate leakage current | V _{GS} = 1.0 V; V _{DS} = 0 V | - | - | 140 | nA |

^[1] In production circuit with 1205 Ω gate feed resistor.

Table 7. RF Characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 80 mA (driver stage); $P_{L(AV)}$ = 8 W unless otherwise specified, measured in an Ampleon straight lead production circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------|------------------------------|---|------|-----|------|------|
| Test signa | l: single carrier W-CDMA [1] | | | | | |
| Gp | power gain | f = 1877.5 MHz; I _{Dq2} = 200 mA (final stage) | - | 29 | - | dB |
| | | f = 2167.5 MHz; I _{Dq2} = 240 mA (final stage) | 26.5 | 28 | 29.5 | dB |
| η_{D} | drain efficiency | f = 1877.5 MHz; I _{Dq2} = 200 mA (final stage) | - | 26 | - | % |
| | | f = 2167.5 MHz; I _{Dq2} = 240 mA (final stage) | 18 | 24 | - | % |

^[2] In production circuit with 460 Ω gate feed resistor.

Table 7. RF Characteristics ... continued

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 80 mA (driver stage); $P_{L(AV)}$ = 8 W unless otherwise specified, measured in an Ampleon straight lead production circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------|---|------|-----|-------|------|
| RLin | input return loss | f = 1877.5 MHz; I _{Dq2} = 200 mA (final stage) | - | -18 | - | dB |
| | | f = 2167.5 MHz; I _{Dq2} = 240 mA (final stage) | - | -20 | -10 | dB |
| ACPR _{5M} | adjacent channel power ratio | f = 1877.5 MHz; I _{Dq2} = 200 mA (final stage) | - | -38 | - | dBc |
| | (5 MHz) | f = 2167.5 MHz; I _{Dq2} = 240 mA (final stage) | - | -36 | -28.5 | dBc |
| PARO | output peak-to-average ratio | f = 1877.5 MHz; I _{Dq2} = 200 mA (final stage) | - | 8.6 | - | dB |
| | | f = 2167.5 MHz; I _{Dq2} = 240 mA (final stage) | 4.6 | 7 | - | dB |
| Test signa | al: CW [2] | | | | | |
| $\Delta\phi_{s21}$ | phase response difference | between sections | -15 | - | +15 | deg |
| $\Delta s_{21} ^2$ | insertion power gain difference | between sections | -0.6 | - | +0.6 | dB |

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

8. Application information

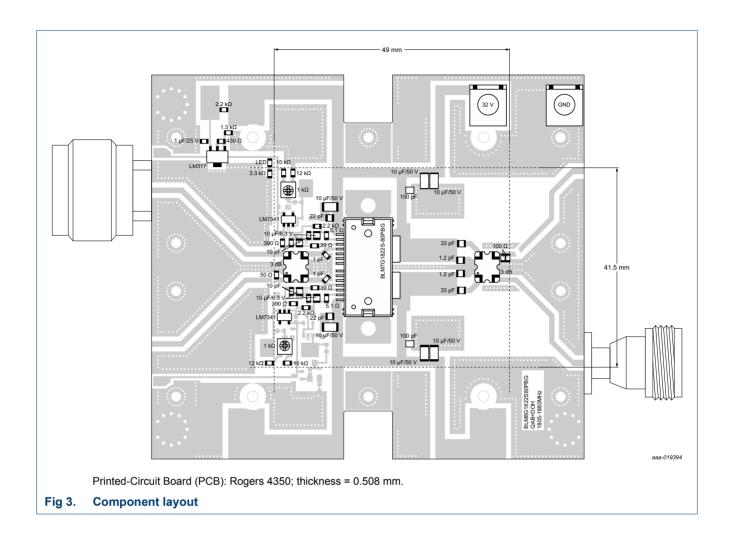
Table 8. Typical performance

 $T_{\rm case} = 25$ °C; $V_{\rm DS} = 32$ V; $I_{\rm Dq} = 544$ mA (driver and final stages); Test signal: 1-carrier W-CDMA; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF; unless otherwise specified, measured in an Ampleon, f = 1805 MHz to 1880 MHz, quadrature combined Class AB application circuit (see Figure 3 and Figure 4).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------|---------------------------------------|---|-----|------|-----|-------|
| P _{L(1dB)} | output power at 1 dB gain compression | f = 1840 MHz | - | 48.9 | - | dBm |
| P _{L(3dB)} | output power at 3 dB gain compression | f = 1840 MHz | - | 49.6 | - | dBm |
| η_{D} | drain efficiency | 12 dB OBO (P _{L(AV)} = 37.6 dBm); f = 1840 MHz | - | 13.7 | - | % |
| Gp | power gain | P _{L(AV)} = 37.6 W; f = 1840 MHz | - | 29 | - | dB |
| B _{video} | video bandwidth | P _{L(AV)} = 41.6 W; 2-tone CW; f = 1840 MHz | - | 90 | - | MHz |
| G _{flat} | gain flatness | P _{L(AV)} = 37.6 W | - | 0.2 | - | dB |
| ΔG/ΔT | gain variation with temperature | f = 1840 MHz [1] | - | 0.04 | - | dB/°C |
| S ₁₂ ² | isolation | between sections A and B; $P_{L(AV)} = 9 \text{ dBm; } f = 1840 \text{ MHz;}$ measured on production board; $I_{Dq} = 560 \text{ mA (both sections)}$ | - | 25 | - | dB |
| K | Rollett stability factor | $T_{case} = -40 ^{\circ}\text{C}$; f = 0.1 GHz to 3 GHz | - | > 1 | - | |

^[1] For both sections (S-parameters measured with load-pull jig).

^[2] f = 2170 MHz.

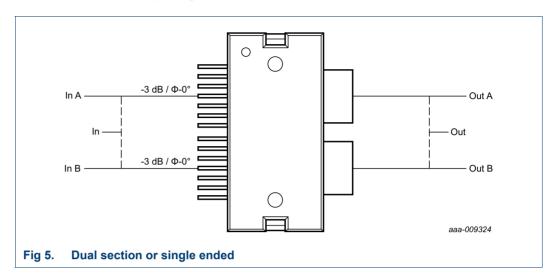


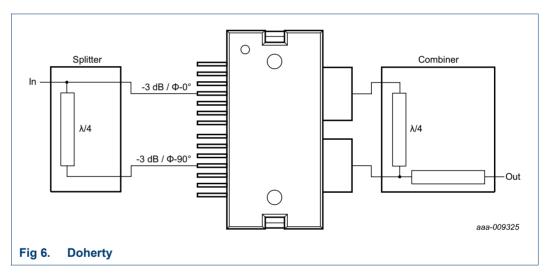
Product data sheet BLM7G1822S-80PB_S-80PBG bias 32 V 1 2.2 kΩ ~5.1 V BLM7G1822S-80PG PathA V_{DS(A1} 10 µF # # 10 µF 50 V 430 Ω 10 kΩ Q VDS(A2) 1.3 kΩ 1 kΩ V_{GS(A1)} All information provided in this document is subject to legal disclaimers 10 pF ATC600F LM7341 Final clamped RF sense FET 100 pF ATC600F Driver clamped RF_IN_A 12 kΩ n.c. **≟**—i⊢ 33 pF ATC600F RF_OUT_A 16 V_{DS(A2)} RF in n.c. \dashv LED 1.2 pF ATC600F Driver RF power FET Final RF power FET 3.3 kΩ Final 447 Driver 44/ 50 Ω 1.2 pF ATC600F 5 RF_OUT_B V_{DS(B2)} 1 pF 33 pF ATC600F n.c. RF out RF_IN_B 11 Final clamped RF sense FET Drive 10 kΩ clamped RF sense FET 100 pF ATC600F V_{GS(B1} DAC_in_B 1 kΩ V_{GS(B2)} 10 pF ATC600F ©Ampleon Netherlands B.V. 2015. All rights reserved 10 μF 6.3 V √V_{DS(B2)} V_{DS(B1)} 12 kΩ 10 µF 22 pF 50 V 77 ATC600F BLM7G1822S-80PBG PathB V_{DS(B1)} 32 V aaa-019395

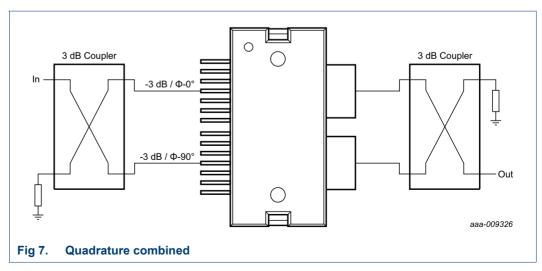
Fig 4.

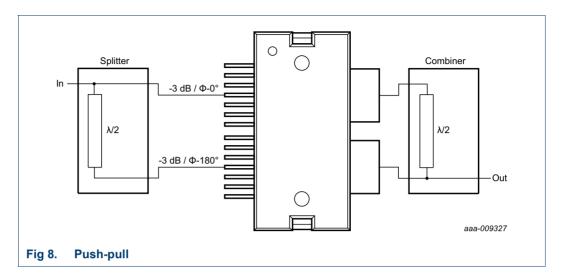
Electrical schematic

8.1 Possible circuit topologies









8.2 Ruggedness in class-AB operation

The BLM7G1822S-80PB and BLM7G1822S-80PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: f = 2140 MHz; V_{DS} = 32 V; I_{Dq1} = 80 mA (each section, driver stage); I_{Dq2} = 180 mA (each section, final stage); P_i = 22 dBm (each section). P_i is measured at CW and corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω load.

8.3 Impedance information

Table 9. Typical impedance

Measured load-pull data per section at 3 dB gain compression point; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $t_p = 100~\mu s$; $\delta = 10$ %; $Z_S = 50~\Omega$; $I_{Dq1} = 80$ mA (driver stage); $I_{Dq2} = 200$ mA (final stage). Typical values unless otherwise specified.

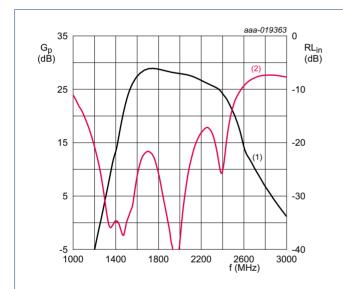
| | tuned for ma | | tuned for maximum power added efficiency | | | | | | | |
|--------|----------------|---------------------|--|------------------|------------------|----------------|---------------------|------|------------------|------------------|
| f | Z _L | G _{p(max)} | PL | η _{add} | AM-PM conversion | Z _L | G _{p(max)} | PL | η _{add} | AM-PM conversion |
| (MHz) | (Ω) | (dB) | (W) | (%) | (deg) | (Ω) | (dB) | (W) | (%) | (deg) |
| BLM7G1 | 1822S-80PB | | | | " | | 1 | | ' | ' |
| 1810 | 2.6 - j5.9 | 29.2 | 48.6 | 49.6 | -2.7 | 5.4 – j5.1 | 30.3 | 47.4 | 56.4 | -5.6 |
| 1840 | 2.7 – j5.8 | 29.9 | 48.5 | 49.3 | -3.8 | 4.9 – j4.8 | 30.9 | 47.5 | 56.3 | -6.2 |
| 1880 | 2.6 - j5.8 | 29.6 | 48.5 | 48.5 | -2.4 | 4.8 – j4.3 | 30.6 | 47.4 | 55.3 | -5.0 |
| 1930 | 2.6 - j5.8 | 29.9 | 48.4 | 47.9 | -1.1 | 4.3 - j4.2 | 30.8 | 47.4 | 54.3 | -2.9 |
| 1960 | 2.6 - j5.8 | 29.9 | 48.4 | 48.0 | -1.0 | 4.2 – j4.2 | 30.8 | 47.5 | 54.3 | -2.2 |
| 1990 | 2.6 – j5.7 | 29.6 | 48.3 | 47.5 | -2.1 | 3.6 – j4.0 | 30.4 | 47.4 | 53.8 | -3.9 |
| 2110 | 2.6 - j5.8 | 29.8 | 48.3 | 48.3 | -3.6 | 3.1 – j4.1 | 30.2 | 47.4 | 52.6 | -4.7 |
| 2140 | 2.6 - j5.8 | 29.8 | 48.3 | 48.6 | -4.1 | 3.1 – j4.7 | 30.3 | 47.6 | 51.9 | -3.9 |
| 2170 | 2.6 - j5.8 | 29.5 | 48.2 | 46.0 | -5.4 | 2.6 - j4.7 | 30.1 | 47.5 | 51.2 | -6.4 |
| BLM7G1 | 1822S-80PBG | | | | | | | | | · |
| 1810 | 3.0 - j8.9 | 29.3 | 48.4 | 50.6 | -1.7 | 5.3 – j7.6 | 30.3 | 47.5 | 57.5 | -5.3 |
| 1840 | 2.7 – j8.7 | 29.1 | 48.3 | 48.4 | -4.4 | 5.0 - j7.5 | 30.2 | 47.5 | 56.9 | -7.5 |
| 1880 | 3.0 – j8.8 | 29.4 | 48.4 | 50.5 | -2.3 | 4.7 – j7.1 | 30.3 | 47.4 | 56.4 | -5.1 |

Table 9. Typical impedance ...continued

Measured load-pull data per section at 3 dB gain compression point; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; t_p = 100 μs; δ = 10 %; Z_S = 50 Ω; I_{Dq1} = 80 mA (driver stage); I_{Dq2} = 200 mA (final stage). Typical values unless otherwise specified.

| | tuned for ma | tuned for maximum output power | | | | | tuned for maximum power added efficiency | | | | |
|-------|----------------|--------------------------------|------|------------------|------------------|----------------|--|------|------------------|------------------|--|
| f | Z _L | G _{p(max)} | PL | η _{add} | AM-PM conversion | Z _L | G _{p(max)} | PL | η _{add} | AM-PM conversion | |
| (MHz) | (Ω) | (dB) | (W) | (%) | (deg) | (Ω) | (dB) | (W) | (%) | (deg) | |
| 1930 | 2.7 – j9.0 | 29.6 | 48.4 | 48.7 | -2.7 | 4.4 – j7.0 | 30.6 | 47.4 | 56.1 | -5.5 | |
| 1960 | 2.7 – j9.0 | 29.6 | 48.4 | 48.7 | -2.7 | 4.0 – j6.8 | 30.6 | 47.4 | 55.9 | -5.3 | |
| 1990 | 2.7 – j8.9 | 29.7 | 48.4 | 48.0 | -2.0 | 3.8 – j7.1 | 30.6 | 47.5 | 55.0 | -3.7 | |
| 2110 | 2.7 – j9.5 | 29.9 | 48.5 | 49.5 | -3.4 | 2.8 – j7.6 | 30.6 | 47.6 | 54.9 | -4.2 | |
| 2140 | 2.6 – j9.5 | 29.9 | 48.3 | 49.1 | -4.0 | 2.6 – j7.9 | 30.5 | 47.6 | 53.7 | -3.2 | |
| 2170 | 2.4 – j9.7 | 29.7 | 48.3 | 47.4 | -5.5 | 2.6 – j8.2 | 30.5 | 47.7 | 53.0 | -4.6 | |

8.4 Graphs



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 32 \, V; \, P_{L} = 1.096 \, W;$

 $I_{Dq1} + I_{Dq2}$ = 272 mA (driver and final stages; valid for both sections A and B);

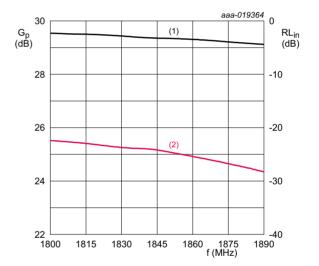
 $V_{GS} = 2.07 \text{ V (driver stage)};$

 V_{GS} = 1.87 V (final stage).

Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 9. Wideband power gain and input return loss as function of frequency; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 32 \, V; \, P_{L} = 3.02 \, W;$

 I_{Dq1} + I_{Dq2} = 272 mA (driver and final stages; valid for both sections A and B);

 $V_{GS} = 2.07 \text{ V (driver stage)};$

 V_{GS} = 1.87 V (final stage).

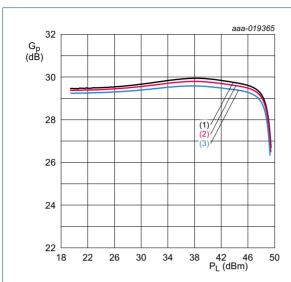
Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 10. In-band power gain and input return loss as function of frequency; typical values

BLM7G1822S-80PB(G)

LDMOS 2-stage power MMIC



 T_{case} = 25 °C; V_{DS} = 32 V;

 $I_{Dq1} + I_{Dq2} = 272$ mA (driver and final stages; valid for both sections A and B);

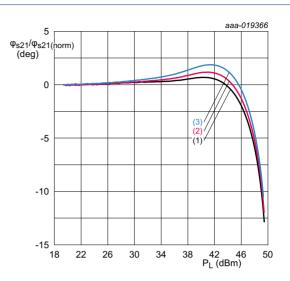
V_{GS} = 2.07 V (driver stage);

V_{GS} = 1.87 V (final stage).

Test signal: pulsed CW.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 11. Power gain as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 32 V;

 $I_{Dq1} + I_{Dq2} = 272$ mA (driver and final stages; valid for both sections A and B);

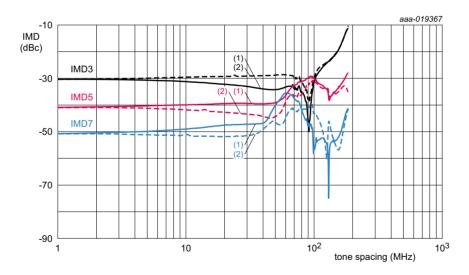
V_{GS} = 2.07 V (driver stage);

V_{GS} = 1.87 V (final stage).

Test signal: pulsed CW.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 12. Normalized phase response as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 32 V; I_{Dq1} + I_{Dq2} = 272 mA (driver and final stages; valid for both sections A and B); V_{GS} = 2.07 V (driver stage); V_{GS} = 1.87 V (final stage).

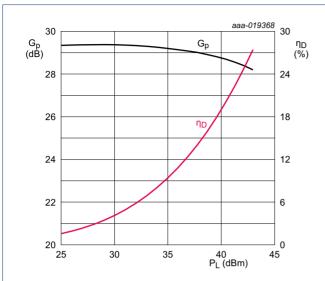
Test signal: 2-tone CW; f_c = 1840 MHz.

- (1) IMD low
- (2) IMD high

Fig 13. Intermodulation distortion as a function of tone spacing; typical values

BLM7G1822S-80PB(G)

LDMOS 2-stage power MMIC



 T_{case} = 25 °C; V_{DS} = 32 V; f = 1840 MHz;

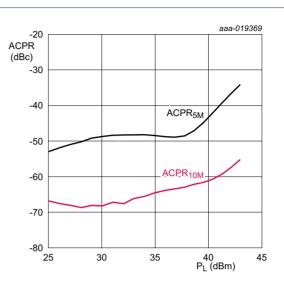
 $I_{Dq1} + I_{Dq2} = 272$ mA (driver and final stages; valid for both sections A and B);

V_{GS} = 2.07 V (driver stage);

V_{GS} = 1.87 V (final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

Fig 14. Power gain and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 32 V; f = 1840 MHz;

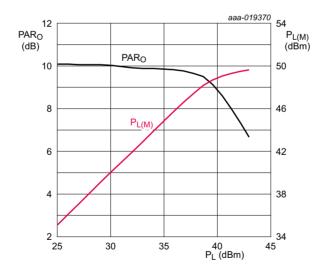
 $I_{Dq1} + I_{Dq2} = 272$ mA (driver and final stages; valid for both sections A and B);

V_{GS} = 2.07 V (driver stage);

 V_{GS} = 1.87 V (final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

Fig 15. Adjacent channel power ratio as a function of output power; typical values



 $T_{case} = 25$ °C; $V_{DS} = 32$ V; f = 1840 MHz; $I_{Dq1} + I_{Dq2} = 272$ mA (driver and final stages; valid for both sections A and B); $V_{GS} = 2.07$ V (driver stage); $V_{GS} = 1.87$ V (final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

Fig 16. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

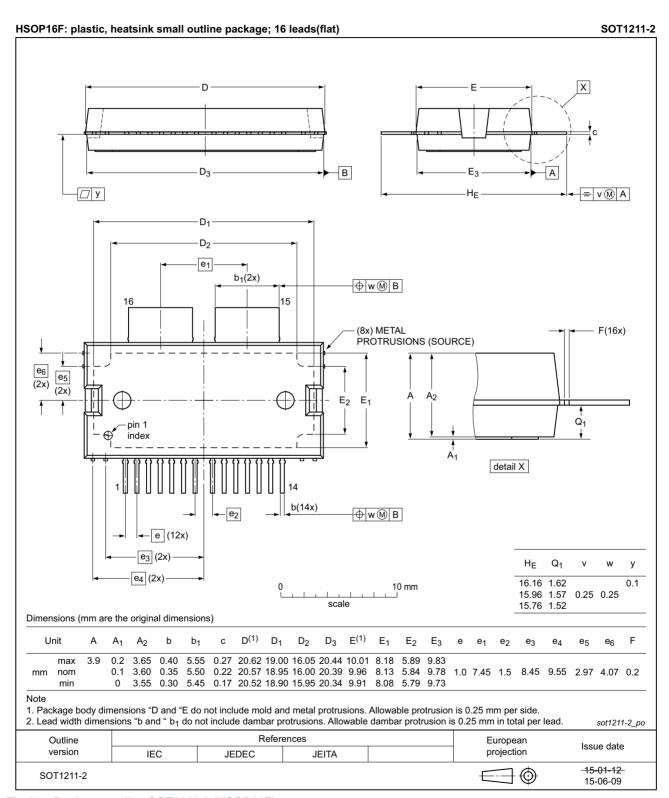


Fig 17. Package outline SOT1211-2 (HSOP16F)

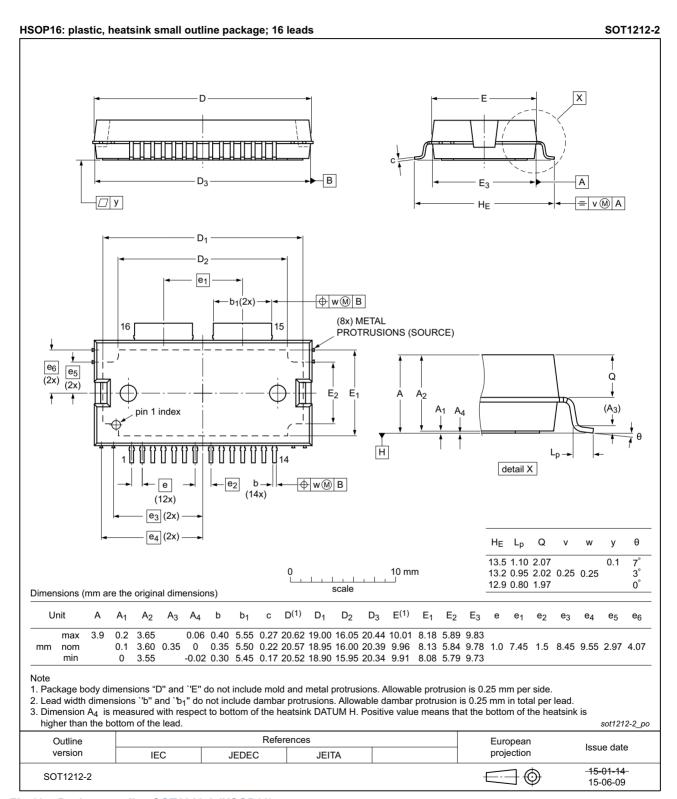


Fig 18. Package outline SOT1212-2 (HSOP16)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 10. Abbreviations

| Description | | | | | |
|--|--|--|--|--|--|
| Amplitude Modulation | | | | | |
| 3rd Generation Partnership Project | | | | | |
| Complementary Cumulative Distribution Function | | | | | |
| Continuous Wave | | | | | |
| Dedicated Physical CHannel | | | | | |
| ElectroStatic Discharge | | | | | |
| Seventh Generation | | | | | |
| Laterally Diffused Metal Oxide Semiconductor | | | | | |
| Monolithic Microwave Integrated Circuit | | | | | |
| Median Time to Failure | | | | | |
| Output Back Off | | | | | |
| Peak-to-Average Ratio | | | | | |
| Phase Modulation | | | | | |
| Voltage Standing-Wave Ratio | | | | | |
| Wideband Code Division Multiple Access | | | | | |
| | | | | | |

12. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|-----------------------------|--|--------------------|---------------|---------------------------------|--|
| BLM7G1822S-80PB_S-80PBG v.2 | 20150901 | Product data sheet | - | BLM7G1822S-80PB_ S-80PBG v.1 | |
| Modifications: | The format of this document has been redesigned to comply with the new identity guidelines of Ampleon Legal texts have been adapted to the new company name where appropriate | | | | |
| BLM7G1822S-80PB_S-80PBG v.1 | 20150824 | Product data sheet | - | - | |

13. Legal information

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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